

# 2SJ166-T2B-VB Datasheet P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	V <sub>GS(th)</sub> (V)	I <sub>D</sub> (mA)			
- 60	3 at V <sub>GS</sub> = - 10 V	- 1 to - 3	-500			

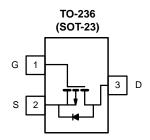
#### **FEATURES**

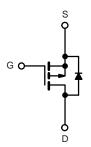




RoHS

- TrenchFET<sup>®</sup> Power MOSFET
- · High-Side Switching
- Low On-Resistance: 3  $\,\Omega\,$
- Low Threshold: 2 V (typ.)
- Fast Swtiching Speed: 20 ns (typ.)
- Low Input Capacitance: 20 pF (typ.)
- Compliant to RoHS Directive 2002/95/EC





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	- 60	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Outline Date Outline	T <sub>A</sub> = 25 °C	I <sub>D</sub>	- 500	mA	
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> = 100 °C		- 350		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	-1500		
Davier Dissingtion 8	T <sub>A</sub> = 25 °C	P <sub>D</sub>	460	mW	
Power Dissipation <sup>a</sup>	T <sub>A</sub> = 100 °C		240		
Maximum Junction-to-Ambient <sup>a</sup>	•	R <sub>thJA</sub>	350	°C/W	
Operating Junction and Storage Temperature Range		T <sub>J,</sub> T <sub>stg</sub>	- 55 to 150	°C	

#### Notes:

- a. Surface mounted on FR4 board.
- b. Pulse width limited by maximum junction temperature.

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			Limits				
Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -10 \mu\text{A}$	- 60			V	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	ľ	
		V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V			± 10	μΑ	
Cata Bady Laakaga		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$			± 200	nA	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}, T_{J} = 85 ^{\circ}\text{C}$			± 500		
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5 \text{ V}$			± 100		
Zava Cata Valtaga Dvain Current		V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V			- 25		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C			- 250		
On-State Drain Current <sup>a</sup>	,	V <sub>GS</sub> = - 10 V, V <sub>DS</sub> = - 4.5 V				4	
	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V, V <sub>DS</sub> = - 10 V	- 600			- mA	
Drain-Source On-Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 25 mA		4			
		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 100 mA		3		Ω	
		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 100 mA, T <sub>J</sub> =125 °C		9			
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 100 mA	80			mS	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = - 100 mA, V <sub>GS</sub> = 0 V			- 1.4	٧	
Dynamic							
Total Gate Charge	Qg			2.0		nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = -15 \text{ V}$ $I_{D} \cong -100 \text{ mA}$		1.2			
Gate-Drain Charge	Q <sub>gd</sub>	10 = - 100 mA		0.8			
Input Capacitance	C <sub>iss</sub>			23		pF	
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}$ f = 1  MHz		10			
Reverse Transfer Capacitance	C <sub>rss</sub>	1 – 1 1411 12		5			
Switching <sup>b</sup>	•		•				
Turn-On Time	t <sub>d(on)</sub>	$V_{DD} = -25 \text{ V}, R_{L} = 150 \Omega$		20		ns	
Turn-Off Time	t <sub>d(off)</sub>	$I_D \cong$ - 200 mA, $V_{GEN} = -10 \text{ V}$ , $R_g = 10 \Omega$		35			

#### Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

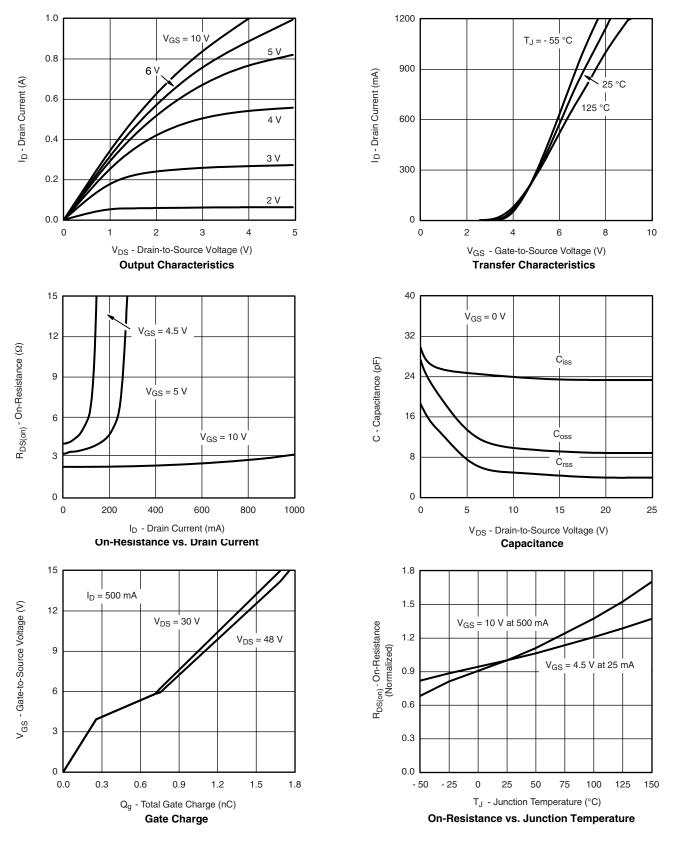
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a. Pulse test: PW  $\leq$  300  $\mu s$  duty cycle  $\leq$  2 %.

b. Switching time is essentially independent of operating temperature.



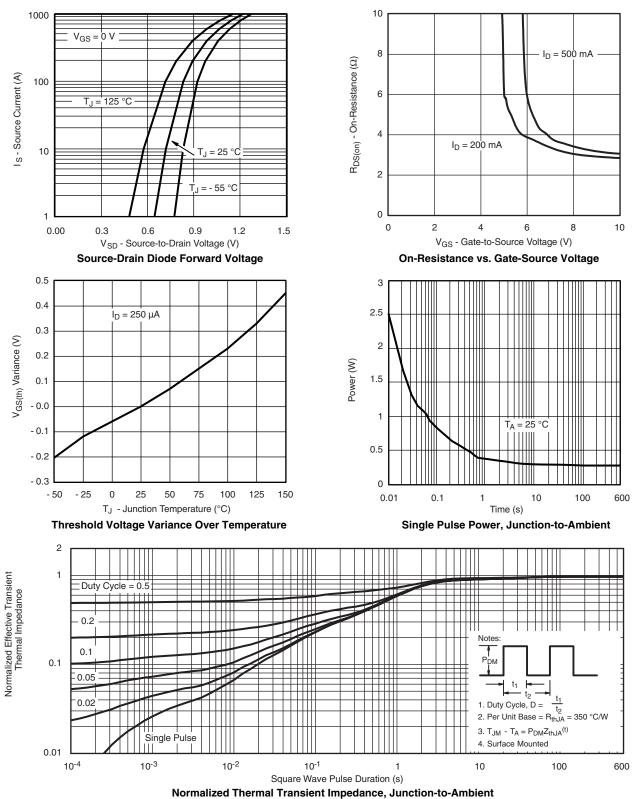
#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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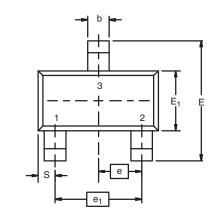
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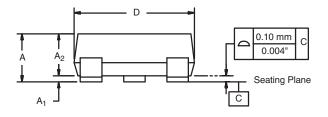


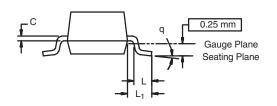
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### SOT-23 (TO-236): 3-LEAD







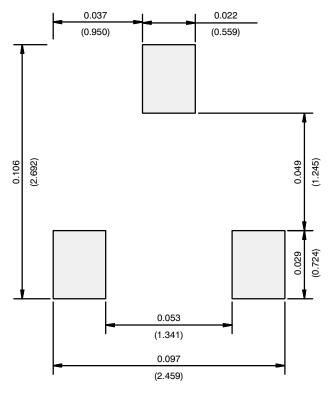
Dim	MILLIMETERS		INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A <sub>1</sub>	0.01	0.10	0.0004	0.004	
A <sub>2</sub>	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E <sub>1</sub>	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e <sub>1</sub>	1.90	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024	
L <sub>1</sub>	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K. 09-	Jul-01				

DWG: 5479

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#### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

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